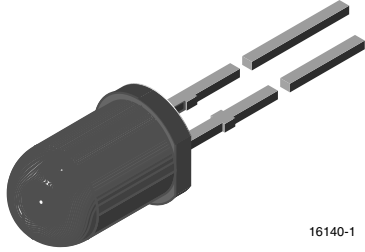


## Silicon PIN Photodiode



16140-1

### DESCRIPTION

BPV10NF is a PIN photodiode with high speed and high radiant sensitivity in black, T-1 $\frac{3}{4}$  plastic package with daylight blocking filter. Filter bandwidth is matched with 870 nm to 950 nm IR emitters.

### FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm):  $\varnothing$  5
- Radiant sensitive area (in mm<sup>2</sup>): 0.78
- Leads with stand-off
- High radiant sensitivity
- Daylight blocking filter matched with 870 nm to 950 nm emitters
- High bandwidth: > 100 MHz at  $V_R = 12$  V
- Fast response times
- Angle of half sensitivity:  $\varphi = \pm 20^\circ$
- Compliant to RoHS Directive 2002/95/EC and in accordance with WEEE 2002/96/EC


**RoHS**  
COMPLIANT

### APPLICATIONS

- High speed detector for infrared radiation
- Infrared remote control and free air data transmission systems, e.g. in combination with TSFFxxxx series IR emitters

### PRODUCT SUMMARY

COMPONENT	$I_{ra}$ ( $\mu$ A)	$\varphi$ (deg)	$\lambda_{0.5}$ (nm)
BPV10NF	60	$\pm 20$	790 to 1050

#### Note

- Test condition see table "Basic Characteristics"

### ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
BPV10NF	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$

#### Note

- MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25$ °C, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	60	V
Power dissipation	$T_{amb} \leq 25$ °C	$P_V$	215	mW
Junction temperature		$T_j$	100	°C
Operating temperature range		$T_{amb}$	- 40 to + 100	°C
Storage temperature range		$T_{stg}$	- 40 to + 100	°C
Soldering temperature	$t \leq 5$ s, 2 mm from body	$T_{sd}$	260	°C
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm <sup>2</sup>	$R_{thJA}$	350	K/W

<b>BASIC CHARACTERISTICS</b> ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 50\text{ mA}$	$V_F$		1.0	1.3	V
Breakdown voltage	$I_R = 100\text{ }\mu\text{A}$ , $E = 0$	$V_{(BR)}$	60			V
Reverse dark current	$V_R = 20\text{ V}$ , $E = 0$	$I_{ro}$		1	5	nA
Diode capacitance	$V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$	$C_D$		11		pF
Open circuit voltage	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 870\text{ nm}$	$V_O$		450		mV
Short circuit current	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 870\text{ nm}$	$I_K$		50		$\mu\text{A}$
Reverse light current	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 870\text{ nm}$ , $V_R = 5\text{ V}$	$I_{ra}$		55		$\mu\text{A}$
	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$ , $V_R = 5\text{ V}$	$I_{ra}$	30	60		$\mu\text{A}$
Temperature coefficient of $I_{ra}$	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 870\text{ nm}$ , $V_R = 5\text{ V}$	$TK_{I_{ra}}$		- 0.1		%/K
Absolute spectral sensitivity	$V_R = 5\text{ V}$ , $\lambda = 870\text{ nm}$	$s(\lambda)$		0.55		A/W
Angle of half sensitivity		$\varphi$		$\pm 20$		deg
Wavelength of peak sensitivity		$\lambda_p$		940		nm
Range of spectral bandwidth		$\lambda_{0.5}$		790 to 1050		nm
Quantum efficiency	$\lambda = 950\text{ nm}$	$\eta$		70		%
Noise equivalent power	$V_R = 20\text{ V}$ , $\lambda = 950\text{ nm}$	NEP		$3 \times 10^{-14}$		$\text{W}/\sqrt{\text{Hz}}$
Detectivity	$V_R = 20\text{ V}$ , $\lambda = 950\text{ nm}$	$D^*$		$3 \times 10^{12}$		$\text{cm}\sqrt{\text{Hz}}/\text{W}$
Rise time	$V_R = 50\text{ V}$ , $R_L = 50\text{ }\Omega$ , $\lambda = 820\text{ nm}$	$t_r$		2.5		ns
Fall time	$V_R = 50\text{ V}$ , $R_L = 50\text{ }\Omega$ , $\lambda = 820\text{ nm}$	$t_f$		2.5		ns

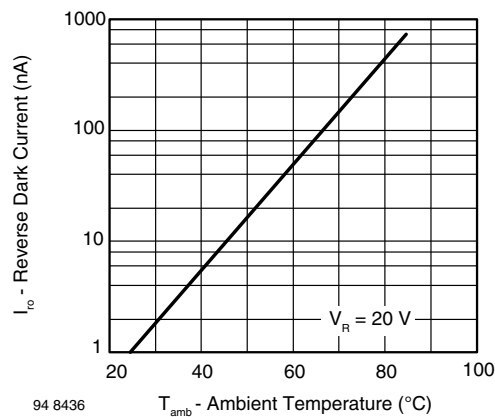
**BASIC CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

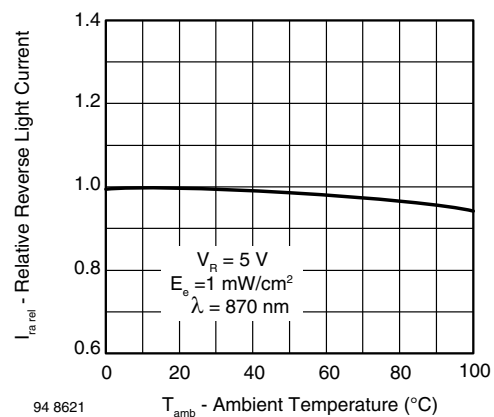


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature

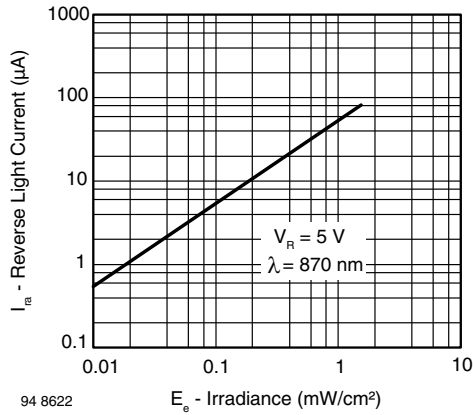


Fig. 3 - Reverse Light Current vs. Irradiance

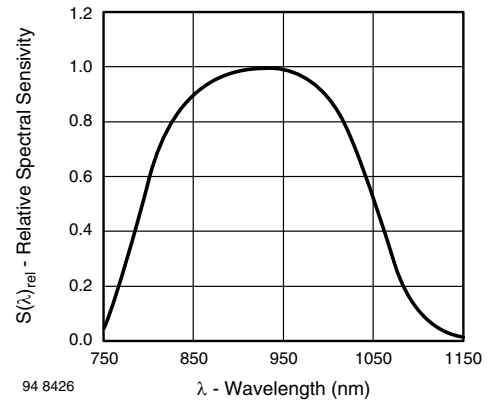


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

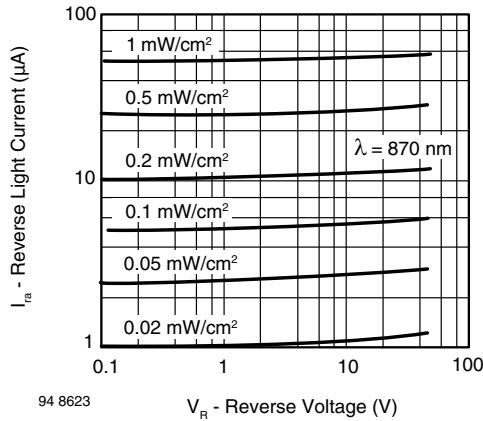


Fig. 4 - Reverse Light Current vs. Reverse Voltage

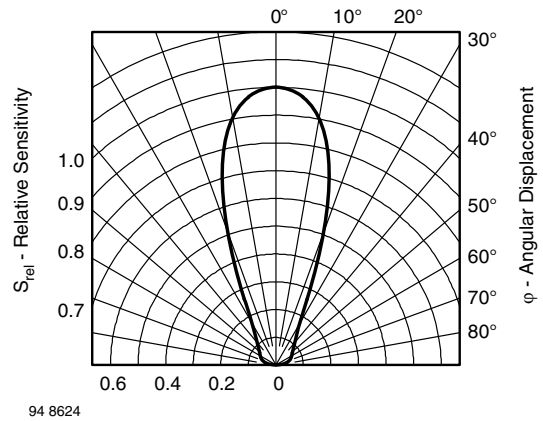


Fig. 7 - Relative Radiant Sensitivity vs. Angular Displacement

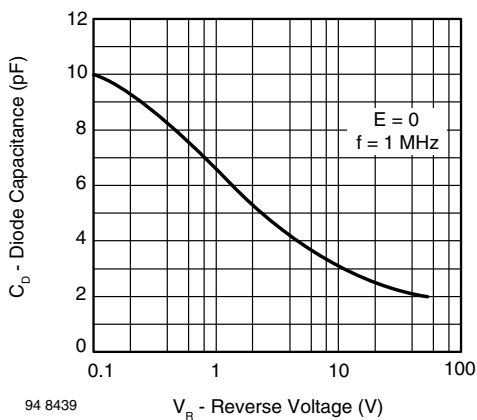
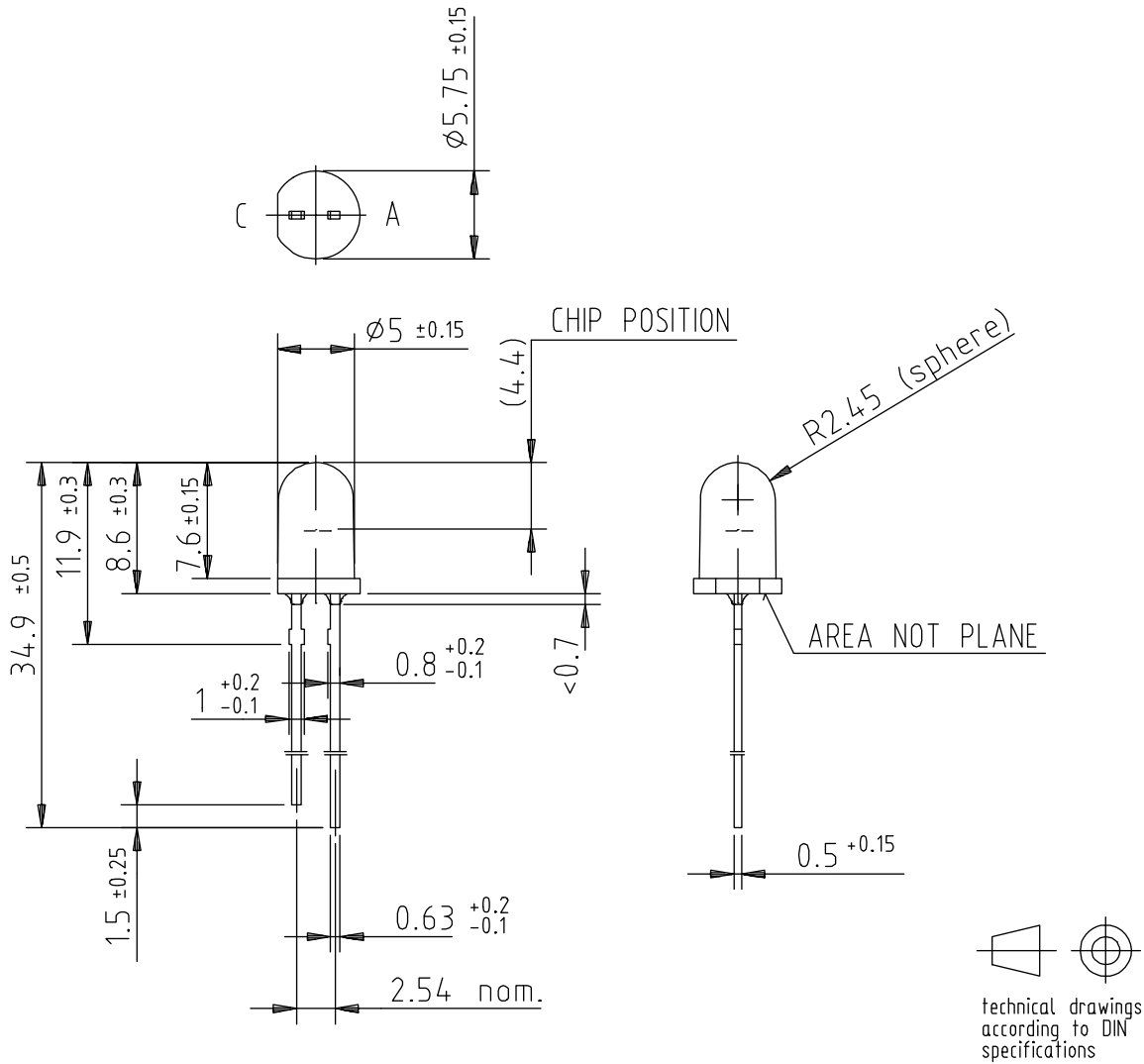


Fig. 5 - Diode Capacitance vs. Reverse Voltage



PACKAGE DIMENSIONS in millimeters



Drawing-No.: 6.544-5185.01-4

96 12198



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